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I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail in an envelope addressed to: Assistant Commissioner for Patents, Fashington, D.C. 20231.

Date: May 14, 2001

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant

Thomas Peter Haneder et al.

Appl. No.

09/801,209

Filed

March 7, 2001

Title

Ferroelectric Transistor, Use Therof in a Memory Cell Configuration

and Method of Producing the Ferroelectric Transistor

Art Unit

<u>LETTER</u>

Hon. Commissioner of Patents and Trademarks, Washington, D.C. 20231

Sir:

The above-mentioned new patent application was filed on March 7, 2001 without a signed oath or declaration, under the provision of 37 C.F.R. 1.53(f).

In accordance with the above-mentioned rule, enclosed herewith is the original signed declaration.

The undersigned hereby states that the application filed in the Patent and Trademark Office is the application which the inventor(s) executed by signing the declaration. 601.01(a).

The fee required for the late filing of an oath or declaration in the amount of \$130.00 is also enclosed.

Respectfully submitted,

OKY L. MAYBACK

3 NO. 40.719

/mjb

Date: May 14, 2001

Lerner and Greenberg, P.A.

Post Office Box 2480

Hollywood, FL 33022-2480

Tel:

(954) 925-1100

Fax:

(954) 925-1101